

1	MAGNETIC BUBBLES	185.08	..With volatile signal storage device
2	.Disposition of elements		
3	..Lattice	185.09	..Error correction (e.g., redundancy, endurance)
4	.Decoder		
5	.Logic	185.1	..Extended floating gate
6	.Rotating field circuits	185.11	..Bank or block architecture
7	.Detectors	185.12	...Parallel row lines (e.g., page mode)
8	..Magnetoresistive		
9	..Hall effect	185.13	...Global word or bit lines
10	..Optical	185.14	..Program gate
11	.Generators	185.15	..Weak inversion injection
12	..By splitting	185.16	..Virtual ground
13	.Plural interacting paths	185.17	..Logic connection (e.g., NAND string)
14	..Closed loop		
15	...Major-minor	185.18	.Particular biasing
16	..With switch at interacting point	185.19	..Multiple pulses (e.g., ramp)
17	...Idler switch	185.2	..Reference signal (e.g., dummy cell)
18	..Boundary	185.21	...Sensing circuitry (e.g., current mirror)
19	.Conductor propagation		
20	..Including A.C. signal	185.22	...Verify signal
21	..Three phase signals	185.23	..Drive circuitry (e.g., word line driver)
22	.One's and zero's		
23	.Plural direction propagation	185.24	..Threshold setting (e.g., conditioning)
24	..Nonsequential		
25	.Velocity	185.25	..Line charging (e.g., precharge, discharge, refresh)
26	..Turns		
27	.Bias	185.26	..Floating electrode (e.g., source, control gate, drain)
28	..Variable		
29	.Strip domain	185.27	..Substrate bias
30	.In-plane field (nonrotating)	185.28	..Tunnel programming
31	.Different size bubbles	185.29	..Erase
32	.Multiple magnetic layer	185.3	...Over erasure
33	.Magnetic storage material	185.31	...Nonsubstrate discharge
34	..Amorphous	185.32Radiation erasure
35	.Guide structure	185.33	...Flash
36	..Ion implantation	45	ANALOG STORAGE SYSTEMS
37	..Slots or rails	46	.Resistive
38	..Zigzag	47	.Thermoplastic
39	..Overlays	48	.Magnetic
40	...On opposite sides of storage medium	49.1	ASSOCIATIVE MEMORIES (CONTENT ADDRESSABLE MEMORY-CAM)
41	...Dots	49.11	.Flip-Flop
42	...Wedges	49.12	.Capacitor cell
43	...Chevrons	49.13	.Ferroelectric cell
44	...Rectangular bars	50	.Magnetic cell
185.01	FLOATING GATE	49.15	.Auxiliary lines
185.02	.Disturbance control	49.16	.Segmented/Partitioned of cells
185.03	.Multiple values (e.g., analog)	49.17	.Compare/Search/Match circuit
185.04	.Data security	49.18	.Priority encoders
185.05	.Particular connection	51	FORMAT OR DISPOSITION OF ELEMENTS
185.06	..Segregated columns	52	HARDWARE FOR STORAGE ELEMENTS
185.07	..Cross-coupled cell	53	.Shields

54	.Ground plane	105	..Diodes
55	.Magnetic	106	RADIANT ENERGY
56	..Spacers	107	.Chemical fluids
57	..Keeper	108	.Liquid crystal
58	..Slot	109	.Photoconductive and ferroelectric
59	..Embedded conductor		
60	..Air gap	110	.Electroluminescent and photoconductive
61	..Hairpin conductor	111	.Electroluminescent
62	..Permanent magnet	112	.Photoconductive
63	INTERCONNECTION ARRANGEMENTS	113	.Amorphous
64	.Optical	114	.Semiconductive
65	.Ferroelectric	115	..Diodes
66	.Magnetic	116	.Plasma
67	..Plural diagonal	117	.Ferroelectric
68	..Tree	118	.Electron beam
69	..Crossover	119	.Color centers
70	..Woven	120	INFORMATION MASKING
71	.Negative resistance	121	.Polarization
72	.Transistors or diodes	122	..Magneto-optical
73	RECIRCULATION STORES	123	.Bragg cells
74	.Magnetic	124	.Diffraction
75	.Stepwise	125	..Holograms
76	.Delay lines	126	.Thermoplastic
77	.Plural paths	127	.Transparency
78	PLURAL SHIFT REGISTER MEMORY DEVICES	128	.Electron beams
80	MAGNETIC SHIFT REGISTERS	129	SYSTEMS USING PARTICULAR ELEMENT
81	.Bidirectional	130	.Three-dimensional magnetic array
82	.Two cells per bit	131	.Two magnetic cells per bit
83	.SiPo/PiSo	132	.Different size cores
84	.Core in transfer loop	133	.Cells of diverse coercivity
85	.Continuous	134	.Continuous cells
86	..Plated wire	135	..Elongated or bar-shaped cell
87	.Thin film	136	...Twisters
88	..Domain tip	137	...Tubular
89	.Logic	138	...Chain
90	.Multiaperture cell	139	...Plated wire
91	..Ladder	140	.Multiaperture cell
92	..With other type core	141	..Aperture plate
93	.Including delay means	142	..Aperture with transverse axis
94	READ ONLY SYSTEMS (I.E.. SEMIPERMANENT)	143	...Biax
95	.With override (i.e., latent images)	144	..Same size apertures
96	.Fusible	145	.Ferroelectric
97	.Magnetic	146	.Electrets
98	..Random core	147	.Persistent internal polarization (PIP)
99	..Random wiring	148	.Resistive
100	.Resistive	149	.Capacitors
101	.Inductive	150	..Inherent
102	.Capacitative	151	.Molecular or atomic
103	.Semiconductive	152	..Nuclear induction or spin echo
104	..Transistors	153	.Electrochemical
		154	.Flip-flop (electrical)

155	..Plural emitter or collector	189.09	.Including reference or bias voltage generator
156	..Complementary		
157	.Magnetostrictive or piezoelectric	189.11	.Including level shift or pull-up circuit
158	.Magnetoresistive	189.12	.With shift register
159	.Negative resistance	190	.For complementary information
160	.Superconductive	191	.Signals
161	..Thin film	192	..Radio frequency
162	..Josephson	193	..Strobe
163	.Amorphous (electrical)	194	..Delay
164	.Electrical contacts	195	..Inhibit
165	..Coherer	196	...Sense/inhibit
166	..Relay	197	..Microwave
167	.Simulating biological cells	198	..Transmission
168	.Ternary	199	..Coincident A.C. signal with pulse
169	.Gunn effect		
170	.Hall effect	200	.Bad bit
171	.Magnetic thin film	201	.Testing
172	..Isotropic	202	.Complementing/balancing
173	..Multiple magnetic storage layers	203	.Precharge
174	.Semiconductive	204	.Accelerating charge or discharge
175	..Diodes	205	.Flip-flop used for sensing
176	..Silicon on sapphire (SOS)	206	.Noise suppression
177	..Bioplar and FET	207	.Differential sensing
178	..Ion implantation	208	..Semiconductors
179	..Plural emitter or collector	209	..Magnetic
180	..Four layer devices	210.1	..Reference or dummy element
181	..Complementary conductivity	210.11	...Compensate signal
182	..Insulated gate devices	210.12	...Voltage setting
183	...Charge coupled	210.13	...Common bit line
184	...Variable threshold	210.14	...Plural elements per reference cell
186	..Single device per bit	210.15	...Structural component of a reference cell
187	..Three devices per bit		
188	..Four or more devices per bit	211	..Temperature compensation
189.011	READ/WRITE CIRCUIT	212	...Semiconductor
189.02	.Multiplexing	213	...Magnetic
189.03	.Plural use of terminal	214	..Particular wiring
189.04	.Simultaneous operations (e.g., read/write)	215	.Optical
189.14	.Common read and write circuit	216	..Holographic
189.15	.Particular read circuit	217	.Electron beam
189.16	.Particular write circuit	218	.Erase
189.17	.Data transfer circuit	219	.SiPo/PiSo
189.18	.Bidirectional bus	220	.Parallel read/write
189.19	.Separate read and write bus	221	.Serial read/write
189.2	.Using different memory types	222	.Data refresh
189.05	.Having particular data buffer or latch	223	.Bridge
189.06	.Including signal clamping	224	.Eddy current
189.07	.Including signal comparison	225	.Minor loop
189.08	.Including specified plural element logic arrangement	225.5	.Including magnetic element
		225.6	.Having bipolar circuit element
		225.7	.Having fuse element
		226	POWERING
		227	.Conservation of power

- 228 .Data preservation
 229 ..Standby power
 230.01 **ADDRESSING**
 230.02 .Multiplexing
 230.03 .Plural blocks or banks
 230.04 ..Alternate addressing (e.g., even/odd)
 230.05 .Multiple port access
 230.06 .Particular decoder or driver circuit
 230.07 ..Including magnetic element
 230.08 .Including particular address buffer or latch circuit arrangement
 230.09 .Combined random and sequential addressing
 231 .Using selective matrix
 232 ..Magnetic
 233.1 .Sync/clocking
 233.11 ..Plural clock signals
 233.12 ..External clock signal modification
 233.13 ..DDR (double data rate) memory
 233.14 ..Initiating signal
 233.15 ..Standby signal
 233.16 ..Write mode signal only
 233.17 ..Read mode signal only
 233.18 ..Burst mode signal
 233.19 ..Common read and write mode signal
 233.5 ..Transition detection
 234 .Optical
 235 ..Page memories
 236 .Counting
 237 .Electron beam
 238 .Cartesian memories
 238.5 .Byte or page addressing
 239 .Sequential
 240 ..Using shift register
 241 ..Detectors
 242 .Current steering
 243 ..Diode
 243.5 .Including magnetic element
 244 **MISCELLANEOUS**
- Any foreign patents or non-patent literature from subclasses that have been reclassified have been transferred directly to FOR Collection listed below. These Collections contain ONLY foreign patents or non-patent literature. Parenthetical references in the Collection titles refer to the abolished subclasses from which these Collections were derived.
- FOR 100 **ASSOCIATIVE MEMORIES (365/49)**
 FOR 101 **READ/WRITE CIRCUIT (365/189.01)**
 .Noise suppression (365/206)
 ..Differential sensing (365/207)
 ...Semiconductor (365/208)
 ...Magnetic (365/209)
 FOR 102 ...Reference or dummy elements (365/210)
ADDRESSING (365/230.01)
 FOR 103 **SYNC/CLOCKING (365/233)**

FOREIGN ART COLLECTIONSFOR 000 **CLASS-RELATED FOREIGN DOCUMENTS**